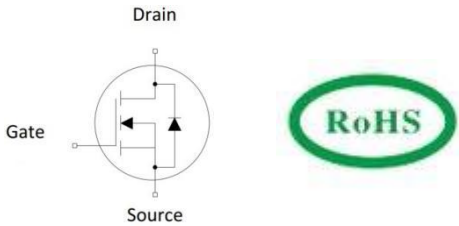


N-channel 600V, 7A, 0.65Ω Super-Junction Power MOSFET

Description Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFET , designed according to the SJ principle. The resulting device has extremely low on resistance,making it especially suitable for applications which require superior power density and outstanding efficiency. Features ◆ Very low FOM $R_{DS(on)} \times Q_g$ ◆ 100% UIS tested ◆ RoHS compliant Applications ◆ Power factor correction (PFC). ◆ Switched mode power supplies (SMPS). ◆ Uninterrupted power supply (UPS).	Product Summary <table> <tr> <td>$V_{DS} @ T_{j,25^\circ C}$</td><td>600V</td></tr> <tr> <td>$R_{DS(on),max}$</td><td>0.65Ω</td></tr> <tr> <td>I_D</td><td>7.0A</td></tr> <tr> <td>$Q_{g,typ}$</td><td>13.1 nC</td></tr> </table>  TO-252  TO-251  TO-220F  N-Channel MOSFET	$V_{DS} @ T_{j,25^\circ C}$	600V	$R_{DS(on),max}$	0.65Ω	I_D	7.0A	$Q_{g,typ}$	13.1 nC
$V_{DS} @ T_{j,25^\circ C}$	600V								
$R_{DS(on),max}$	0.65Ω								
I_D	7.0A								
$Q_{g,typ}$	13.1 nC								

Marking information

Product	Package	Marking	Packing method
RMA60R650SN	TO-252	RMA60R650SN	Reel
RMG60R650SN	TO-251	RMG60R650SN	Tube
RMC60R650SN	TO-220F	RMC60R650SN	Tube

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	600	V
Continuous drain current ($T_C = 25^\circ C$)	I_D	7	A
($T_C = 100^\circ C$)		4.4	A
Pulsed drain current ¹⁾	I_{DM}	21	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ²⁾	E_{AS}	120	mJ
Avalanche current, repetitive ³⁾	I_{AR}	1.2	A
Power Dissipation TO-252 /TO-251 ($T_C = 25^\circ C$)	P_D	63	W
- Derate above 25°C		0.5	W/°C
Power Dissipation TO-220F ($T_C = 25^\circ C$)	P_D	32	W
- Derate above 25°C		0.26	W/°C
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C
Continuous diode forward current	I_S	7	A

Diode pulse current	$I_{S,pulse}$	21	A
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Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO252/TO-251	TO-220F	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2	4	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	68	$^{\circ}\text{C/W}$
Soldering temperature, wave soldering only allowed at leads. (1.6mm from case for 10s)	T_{solder}	260	260	$^{\circ}\text{C}$

Electrical Characteristics $T_c = 25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =250uA	600	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	2.5		4.0	V
Drain cut-off current	I _{DSS}	V _{DS} =600 V, V _{GS} =0 V, T _j = 25°C T _j = 125°C	- -	- 10	1	μA
Gate leakage current, Forward	I _{GSSF}	V _{GS} =30 V, V _{DS} =0 V	-	-	100	nA
Gate leakage current, Reverse	I _{GSSR}	V _{GS} =-30 V, V _{DS} =0 V	-	-	-100	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =3.5 A T _j = 25°C	- - -	0.56	0.65	Ω
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} = 100 V, V _{GS} = 0 V, f = 1MHz	-	493	-	pF
Output capacitance	C _{oss}		-	32	-	
Reverse transfer capacitance	C _{rss}		-	1.6	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 400V, I _D = 3.5A R _G = 25Ω, V _{GS} =10V	-	11.6	-	ns
Rise time	t _r		-	23	-	
Turn-off delay time	t _{d(off)}		-	53	-	
Fall time	t _f		-	35.8	-	
Gate charge characteristics						
Gate to source charge	Q _{gs}	V _{DD} =480 V, I _D =3.5A, V _{GS} =0 to 10 V	-	2.8	-	nC
Gate to drain charge	Q _{gd}		-	4.5	-	
Gate charge total	Q _g		-	13.1	-	
Gate plateau voltage	V _{plateau}		-	5.5	-	V
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =3.5A	-	0.85	-	V
Reverse recovery time	t _{rr}	V _R =50 V, I _F =3.5A, dI _F /dt=100 A/μs	-	201.4	-	ns
Reverse recovery charge	Q _{rr}		-	1.3	-	μC
Peak reverse recovery current	I _{rrm}		-	11.5	-	A

Notes:

1. Limited by maximum junction temperature, maximum duty cycle is 0.75.
2. $I_{AS} = 2A$, $V_{DD} = 50V$, Starting $T_j = 25^{\circ}C$.

Electrical Characteristics Diagrams

Figure 1. Output Characteristics

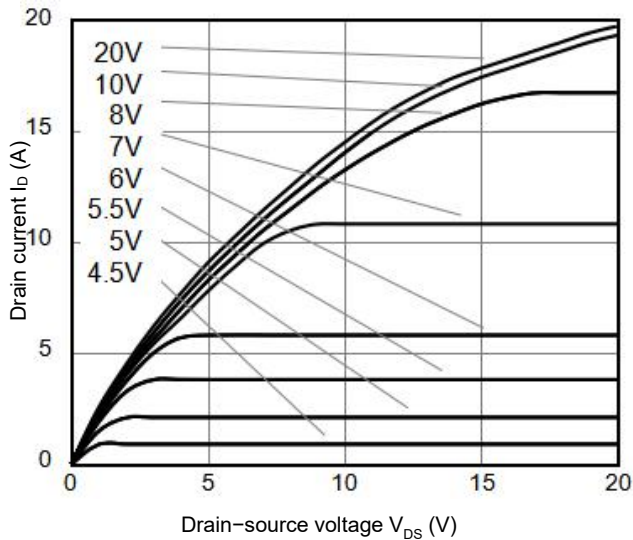


Figure 2. Transfer Characteristics

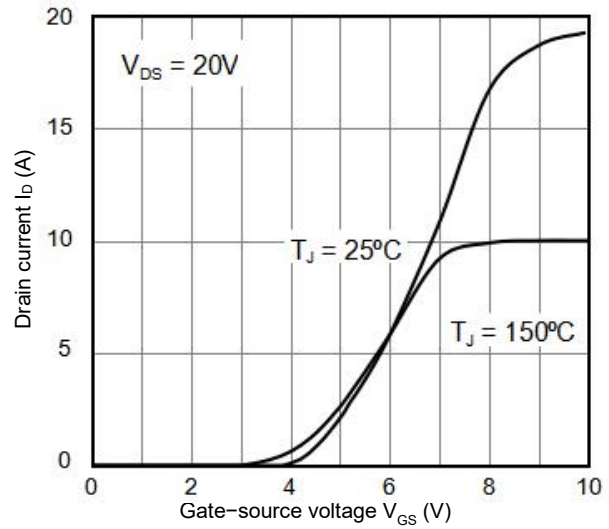


Figure 3. On-Resistance vs. Drain Current

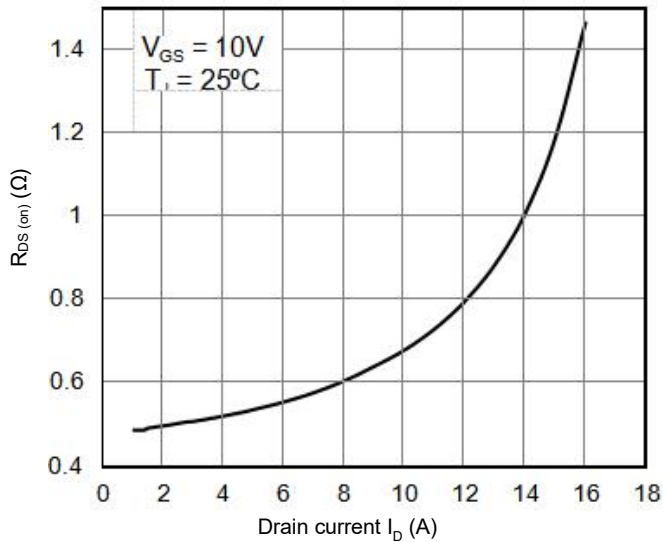


Figure 4. Capacitance Characteristics

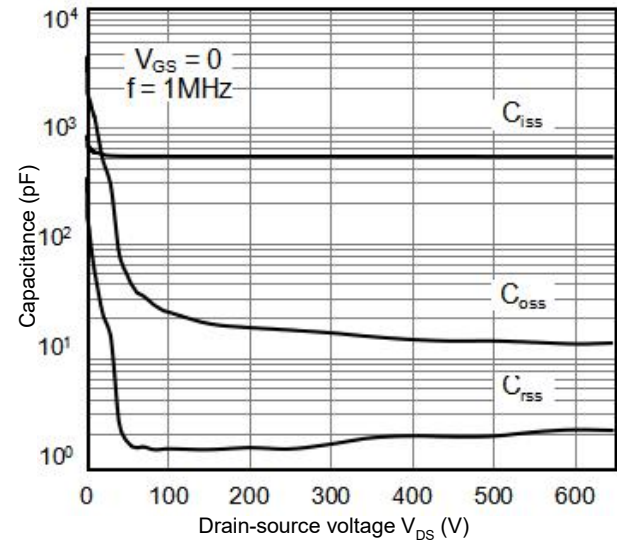


Figure 5. Gate Charge Characteristics

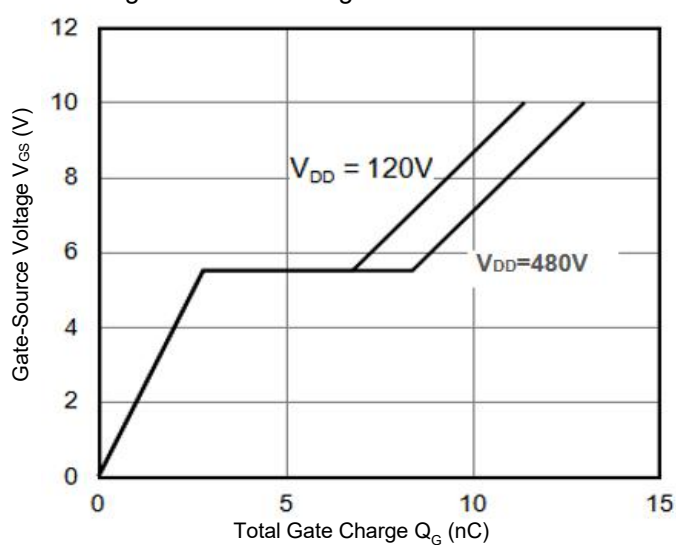


Figure 6. Body Diode Forward Voltage

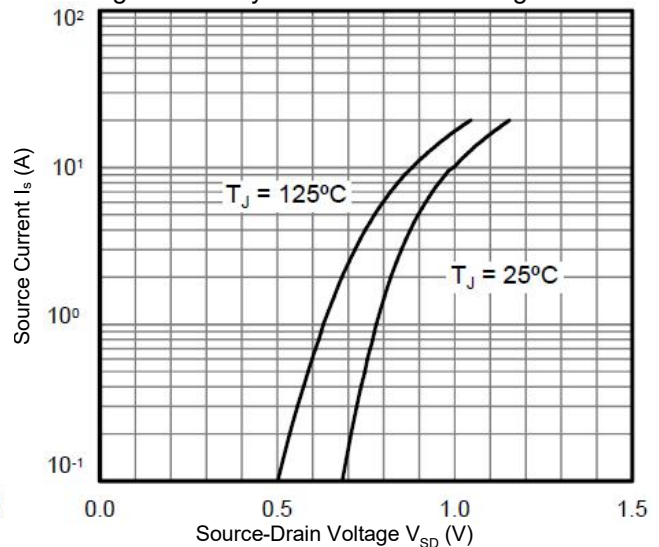


Figure 7. Breakdown Voltage vs. Temperature

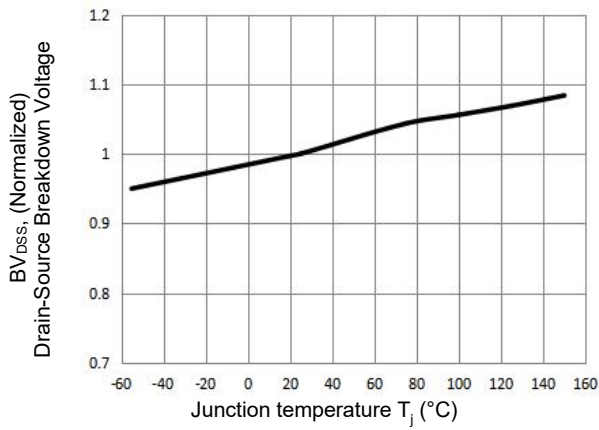


Figure 8. On-Resistance vs. Temperature

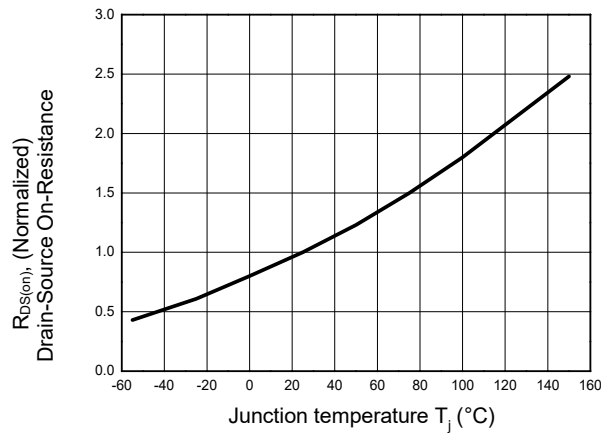


Figure 9. Maximum Safe Operating Area
TO-252/TO-251

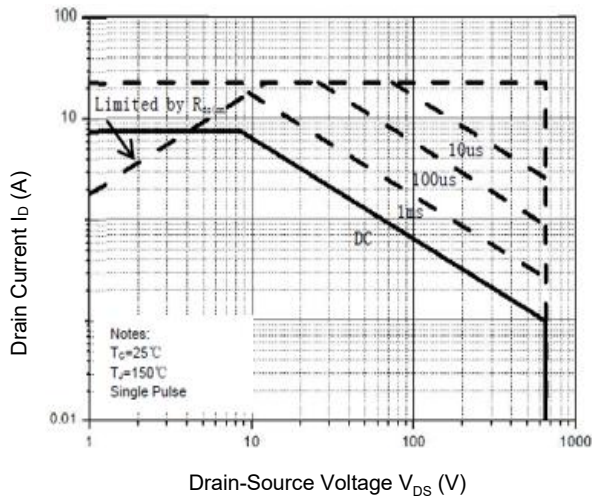
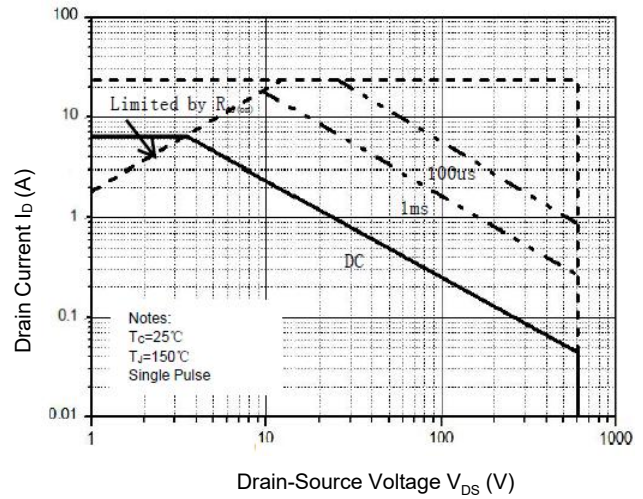
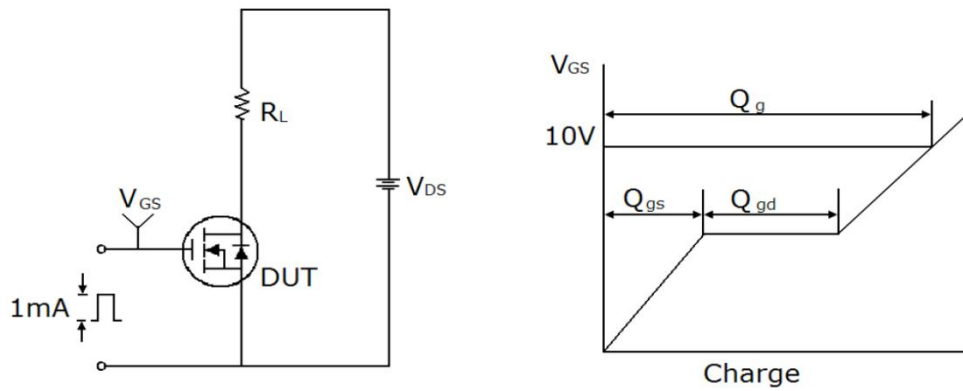


Figure 10. Maximum Safe Operating Area
TO-220F

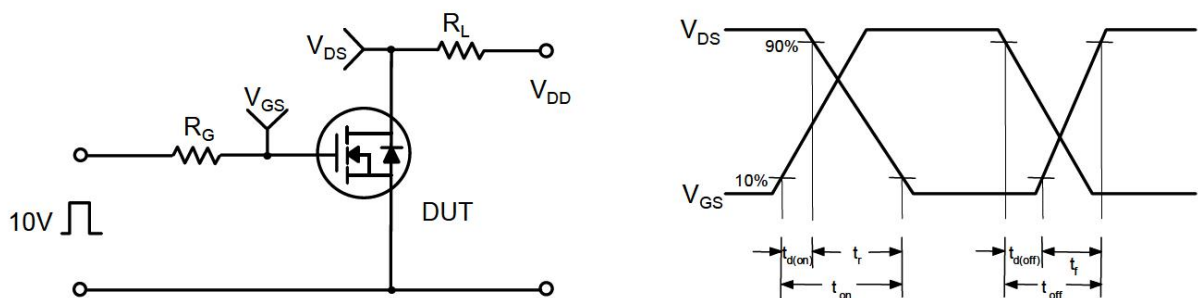


Test Circuits

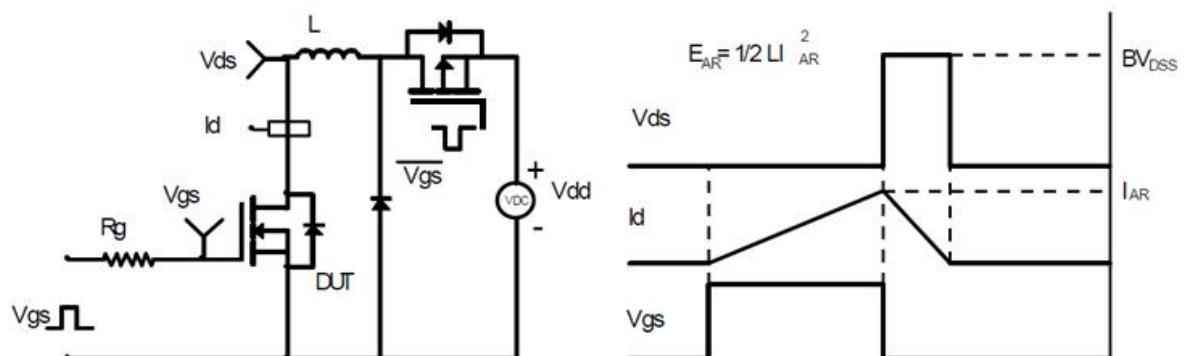
Gate Charge Test Circuit & Waveform



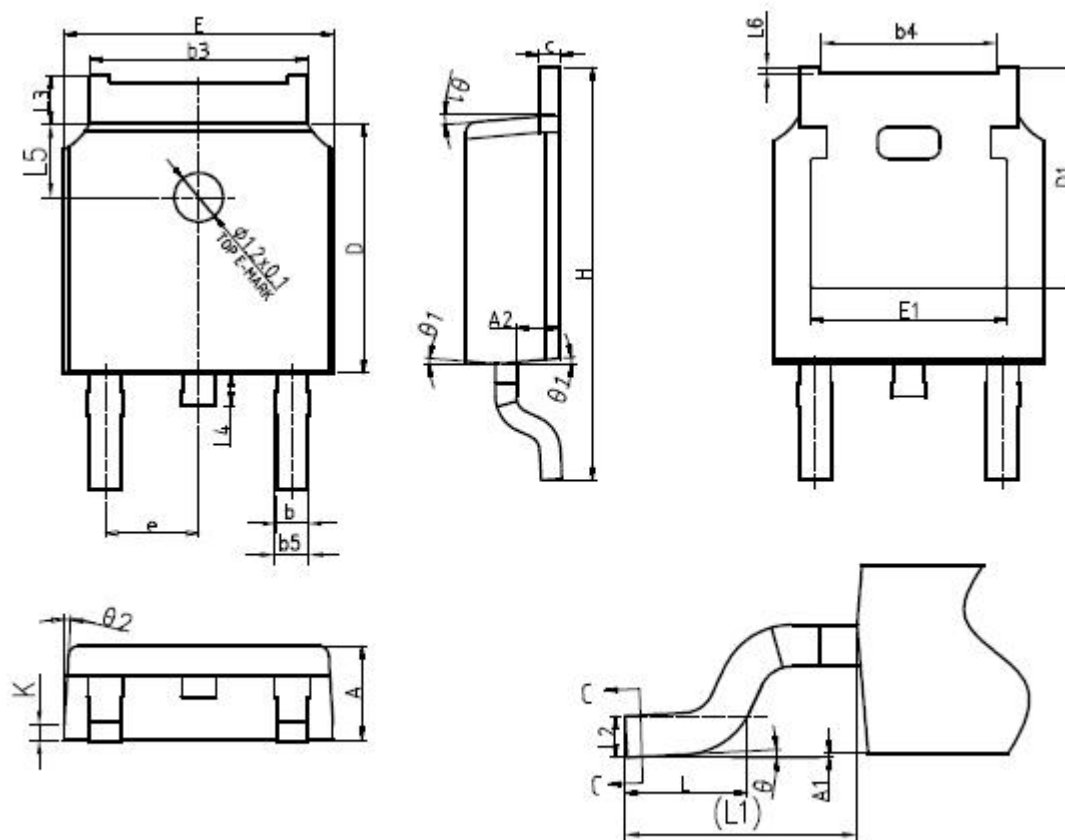
Switching Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveform



Mechanical Dimensions for TO-252

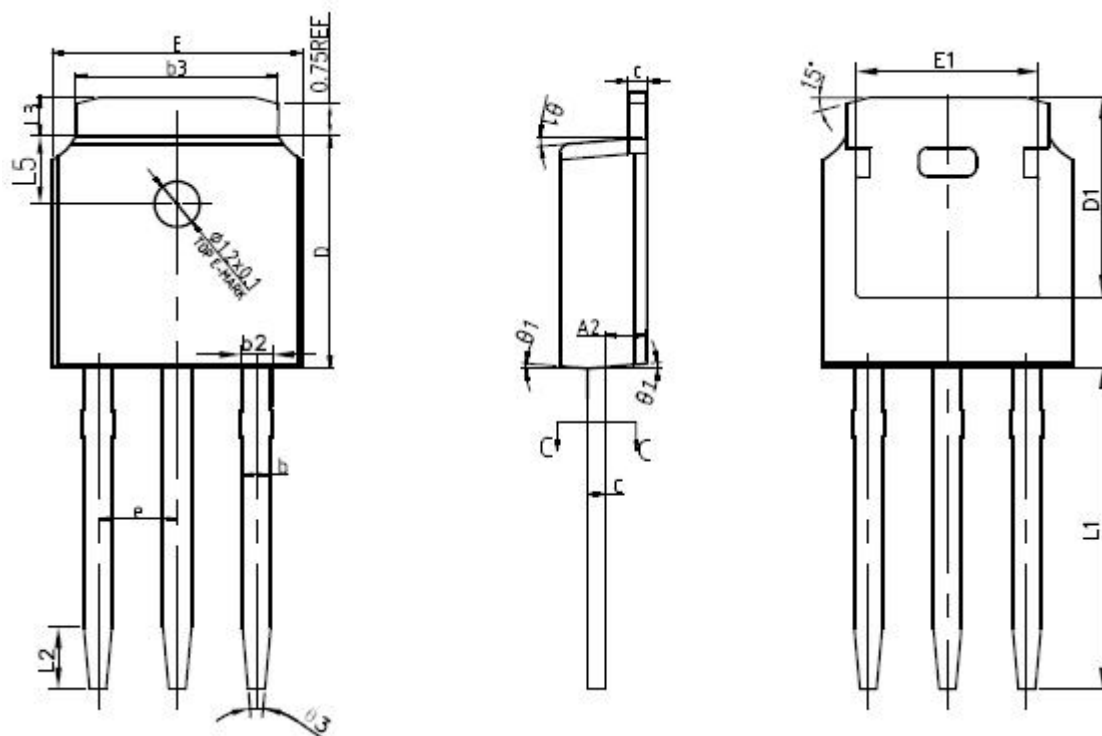


单位: mm

SYMBOL	mm		
	MIN	NOM	MAX
*A	2.20	2.30	2.38
*A1	0.00	-	0.10
A2	0.97	1.07	1.17
*b	0.72	0.78	0.85
b1	0.71	0.76	0.81
*b3	5.23	5.33	5.46
b4	4.27	4.32	4.37
b5	0.72	0.88	0.93
*c	0.47	0.53	0.58
c1	0.46	0.51	0.56
*D	6.00	6.10	6.20
D1	5.30REF		

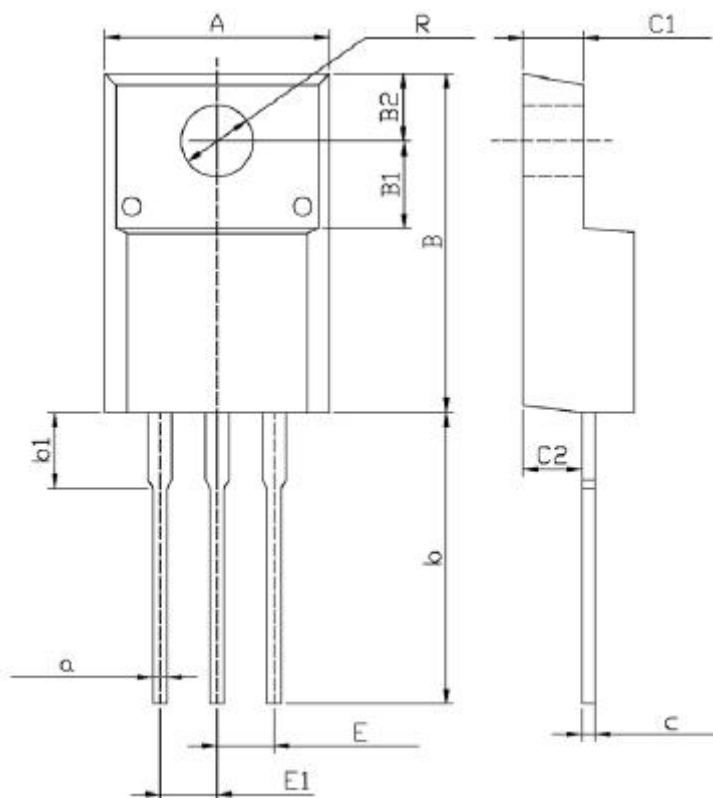
*E	6.50	6.60	6.70
E1	4.70	4.83	4.92
*e	2.286BSC		
L	1.40	1.50	1.70
L1	2.90REF		
L2	0.51BSC		
*L3	0.90	-	1.25
*L4	0.60	0.80	1.00
L5	1.70	1.80	1.90
L6	0	0.047	0.123
θ	0°	-	8°
* θ_1	5°	7°	9°
θ_2	5°	7°	9°
K	0.40REF		

Mechanical Dimensions for TO-251



SYMBOL	MM		
	MIN	NOM	MAX
*A	2.20	2.30	2.38
*A2	0.97	1.07	1.17
*b	0.72	0.78	0.85
b1	0.71	0.76	0.81
*b2	0.72	0.88	0.95
*b3	5.23	5.33	5.46
*c	0.47	0.53	0.58
c1	0.46	0.51	0.56
*D	6.00	6.10	6.20
D1	5.30REF		
*E	6.50	6.60	6.70
E1	4.70	4.83	4.92
*e	2.286BSC		
*L1	9.20	9.40	9.60
L2	1.25	1.35	1.45
*L3	0.90	1.02	1.25
L5	1.70	1.80	1.90
*0 1	5°	7°	9°
0 2	5°	7°	9°
0 3	11°	13°	15°
K	0.40REF		

Mechanical Dimensions for TO-220F



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
C	4.3	4.7	b1	2.9	3.9
A	9.7	10.3	a	0.55	0.75
B	14.7	15.3	E	2.29	2.79
B1	3.8	4.0	E1	2.29	2.79
B2	2.9	3.1	C1	2.5	2.9
R	3.0	3.4	C2	2.5	2.7
b	12.5	13.5	c	0.5	0.7